

**REISSUE APPLICATION
DECLARATION BY THE INVENTOR**

Docket Number
251272US2S RE

As a below named inventor, I hereby declare that:
My residence, post office address and citizenship are stated below next to my name.
I believe I am the original, first and sole inventor (if only one name is listed below) or an original first and joint inventor (if plural names are listed below) of the subject matter which is described and claimed in the below identified patent:

Patent Number
6,346,464

Date Patent Issued
February 12, 2002

Title of Invention

MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

for which a reissue patent is sought on the invention entitled:

MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

the specification of which

☐ is attached hereto

☒ was filed on April 5, 2004 as reissue application number 10/817,623

☒ and (if applicable) was amended on April 5, 2004

I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR 1.56.

We (I) hereby claim foreign priority benefits under 35 USC §119(a)-(d) or §365(b) of any foreign application(s) for patent or inventor's certificate, or §365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT international application having a filing date before that of the application on which priority is claimed. Prior Foreign Application(s):

<u>Application No.</u>	<u>Country</u>	<u>Day/Month/Year</u>	<u>Priority Claimed</u>
11-181687	JAPAN	28 JUNE 1999	YES

We (I) hereby claim the benefit under 35 USC §119(e) of any United States *provisional* application(s) listed below.

Application Number

Filing Date

We (I) hereby claim the benefit under 35 USC §120 of any United States application(s), or §365I of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of 35 USC §112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR §1.56 which became available between the filing date of the prior application and the national or PCT International filing date of this application.

Application Serial No.

Filing Date

Status

6,346,464

12 February 2002

Patented

I verily believe the original patent to be wholly or partly inoperative or invalid, for the reasons described below. (Check all that apply)

☐ by reason of a defective specification or drawing.

☒ by reason of the patentee claiming more or less than he had the right to claim in the patent ... (see below).

☐ by reason of other errors ... (see below).

At least one error upon which reissue is based is described as follows:

As evidenced by the additional limitations of "wherein the irradiating impurity ions is performed to form a junction structure comprising a vertical junction group where a first conductivity-type region and the second conductivity-type region are alternatively arranged vertically to a surface of the semiconductor substrate" that have been added to Claims 1, 2, and 12.

All errors corrected in this reissue application arose without any deceptive intention on the part of the applicant.

Reissue Application Declaration by the Inventor (Continued)

As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected herewith:

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22850

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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine and imprisonment, or both, under 18 U.S.C. 1001, and that such willful false statements may jeopardize the validity of the application, any patent issuing thereon, or any patent to which this declaration is directed.

Full Name of sole or first inventor (given name, family name)

Toru TAKEDA

Signature

Toru Takeda

Date

February 20, 2008

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Tetsujiro TSUNODA

Signature

Tetsujiro Tsunoda

Date

February 27, 2008

Residence

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Citizenship

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Signature

Date

Residence

Citizenship

Post Office Address

☐ Additional joint inventors are named on separately numbered sheets attached hereto.

(OSMMN 03/02)

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